

Silicon NPN Power Transistors

2SD1136

DESCRIPTION

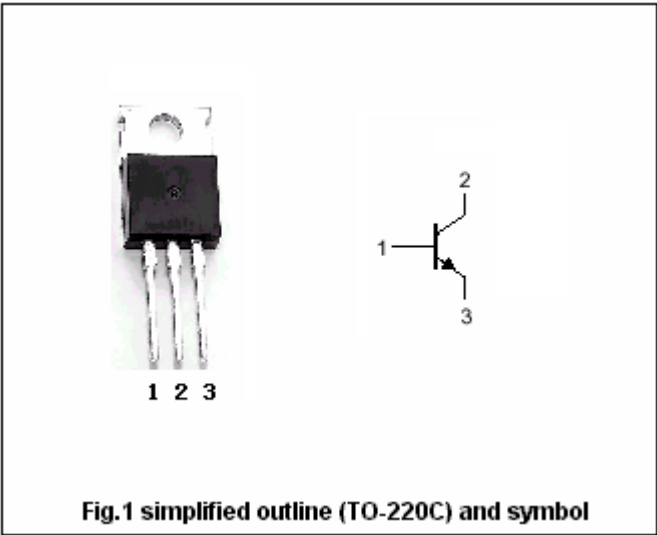
- With TO-220C package
- High collector-base breakdown voltage
: $V_{CBO}=200V(\text{min})$

APPLICATIONS

- For power switching and TV vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		4	A
I_{CM}	Collector current-Peak		5	A
P_C	Collector power dissipation	$T_a=25^{\circ}C$	1.8	W
		$T_C=25^{\circ}C$	30	
T_j	Junction temperature		150	$^{\circ}C$
T_{stg}	Storage temperature		-45~150	$^{\circ}C$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA; I_B=0$	80			V
$V_{(BR)EBO}$	Emitter-base breakdown votage	$I_E=1mA; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4 A; I_B=0.4 A$			1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4 A; I_B=0.4 A$			1.5	V
I_{CEO}	Collector cut-off current	$V_{CE}=200V; I_B=0$			50	μA
I_{EBO}	Collector cut-off current	$V_{EB}=5V; I_C=0$			50	μA
h_{FE}	DC current gain	$I_C=4A; V_{CE}=5V$	20			

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PACKAGE OUTLINE

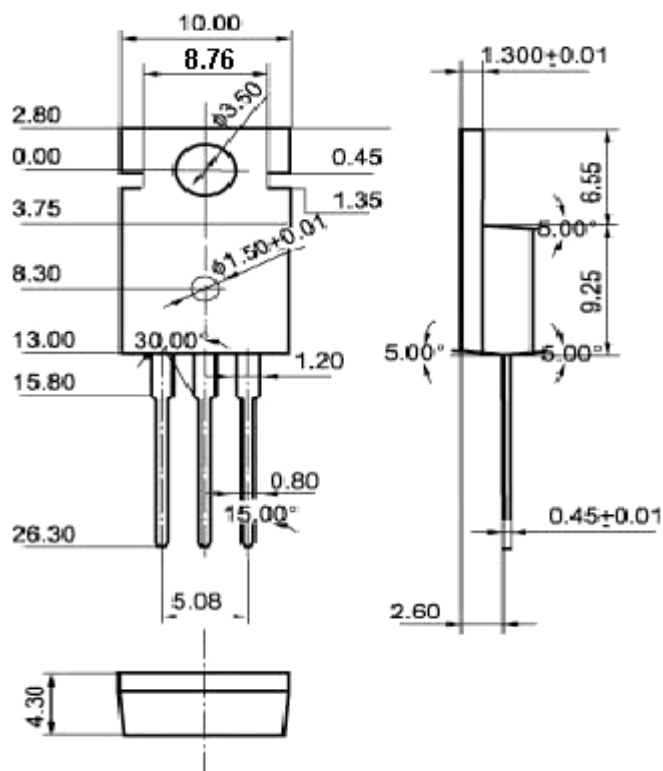


Fig.2 Outline dimensions (unindicated tolerance: ±0.10 mm)